G. Device & Process Modeling, Simulation and Reliability 분과

Room D
함백Ⅱ+Ⅲ(5층)

2016년 2월 23일(화) 10:40-12:40
[TD2-G] Reliability Analysis : Thin-Film Transistors and Field-Effect Transistors
좌장 : 배종욱(LG디스플레이), 이상기(동부하이텍)

TD2-G-1 10:40-10:55
Calculation Method for Negative Bias Illumination Stress-induced Instability in Amorphous IGZO Thin-Film Transistors
Jun Tae Jang, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim
School of Electrical Engineering, Kookmin University

TD2-G-2 10:55-11:10
Investigation of Stress-induced Instability of SiC DMOSFETs
Sangwon Baek[1], Bo Jin[1], Chanoh Park[2], Donghoon Kim[1], and Jeong-Soo Lee[1]
[1]Department of Electrical Engineering, Pohang University of Science and Technology, [2]Division of IT Convergence Engineering, Pohang University of Science and Technology

TD2-G-3 11:10-11:25
Hot Carrier Degradation of Ni related Defects in Sub-100nm Ni-Pt Salicide FinFETs
Seung Min Lee[1,2] and Jungwoo Oh[1,2]
[1]School of integrated technology, Yonsei University, [2]Yonsei Institute of Convergence Technology

TD2-G-4 11:25-11:40
Bias-Temperature Instability of Vertical Poly-Si Thin-Film Transistor
Junyoung Lee[1], Hojoon Lee[1], Bo Jin[1], Jungsik Kim[2], Hyeongwan Oh[1], and Jeong-Soo Lee[1]
[1]Department of Electrical Engineering, Pohang University of Science and Technology, [2]Division of IT Convergence Engineering, Pohang University of Science and Technology

TD2-G-5 11:40-11:55
Compartmentalization of the Physical Origin on the V_T Variation of IGZO TFT under Current Stress by Combining I-V Curve and TCAD
Jae-Young Kim, Sungju Choi, Hara Kang, Jonghwa Kim, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim
School of Electrical Engineering, Kookmin University

TD2-G-6 11:55-12:10
Reliability Characteristics in Junctionless Poly-Si Thin-Film Transistors
Hojoon Lee[1], Junyoung Lee[1], Bo Jin[1], Jungsik Kim[2], Hyeongwan Oh[1], Jiwon Kim[1], and Jeong-Soo Lee[1]
[1]Department of Electrical Engineering, Pohang University of Science and Technology, [2]Division of IT Convergence Engineering, Pohang

University of Science and Technology

TD2-G-7 **12:10-12:25** **5 nm 세대 나노와이어의 Self Heating Effect (SHE) transient 특성 분석**

김현석, 강덕승, 신형철
Inter university Semiconductor Research Center and School of Electrical Engineering and Computer Science, Seoul National University

TD2-G-8 **12:25-12:40** **표면 거칠기를 고려한 5 nm 노드 나노와이어 펫의 채널 반지름에 따른 특성**

손도균, 고 결, 신형철
Inter university Semiconductor Research Center and School of Electrical Engineering and Computer Science, Seoul National University